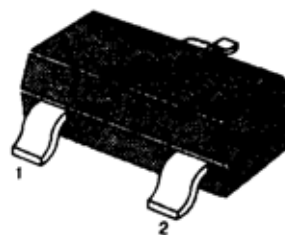


■■ APPLICATION: VHF~UHF Band Low Noise Amplifier Applications.

■■ MAXIMUM RATINGS (Ta=25°C)

SOT-323

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CBO}	20	V
Collector-emitter voltage	V _{CEO}	12	V
Emitter-base voltage	V _{EBO}	3	V
Collector current	I _C	30	mA
Collector Power Dissipation	I _B	15	mA
Junction Temperature	P _C	100	mW
Storage Temperature Range	T _J	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C



1.Base 2.Emitter 3.Collector

■■ ELECTRICAL CHARACTERISTICS (Ta=25°C)

PARAMETER	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITION
DC Current Gain	h _{FE}	80		240		V _{CE} = 5V, I _C = 10mA
Collector Cut-off Current	I _{CBO}			1	μA	V _{CB} = 10V, I _E =0
Emitter Cut-off Current	I _{EBO}			1	μA	V _{EB} = 1V, I _C =0
Collector-Base Breakdown Voltage	BV _{CBO}	20			V	I _C = 0.1mA, I _E =0
Collector-Emitter Breakdown Voltage	BV _{CEO}	12			V	I _C = 1mA, I _B =0
Emitter-Base Breakdown Voltage	BV _{EBO}	3			V	I _E = 0.1mA, I _C =0
Gain bandwidth product	f _T	5	7		GHz	I _C = 10mA, V _{CE} = 5V
Common Base Output Capacitance	C _{ob}		0.7		pF	V _{CB} = 5V, I _E =0, f = 1MHz
Common Base Output Capacitance	C _{re}		0.45	0.9	pF	V _{CB} = 5V, I _E =0, f = 1MHz
Noise Figure	N _{F1}			1	dB	I _C = 3mA, V _{CE} = 5V, f= 500MHz
	N _{F2}		1.1	2	dB	I _C = 3mA, V _{CE} = 5V, f= 1GHz

■■ h_{FE} Classification And Marking

Print Mark	M1	M2
Classification	O	Y
h _{FE}	80~160	120~240